

SHINDENGEN

HVX-2 Series Power MOSFET

N-Channel Enhancement type

**2SK2667
(F3W90HVX2)**

900V 3A

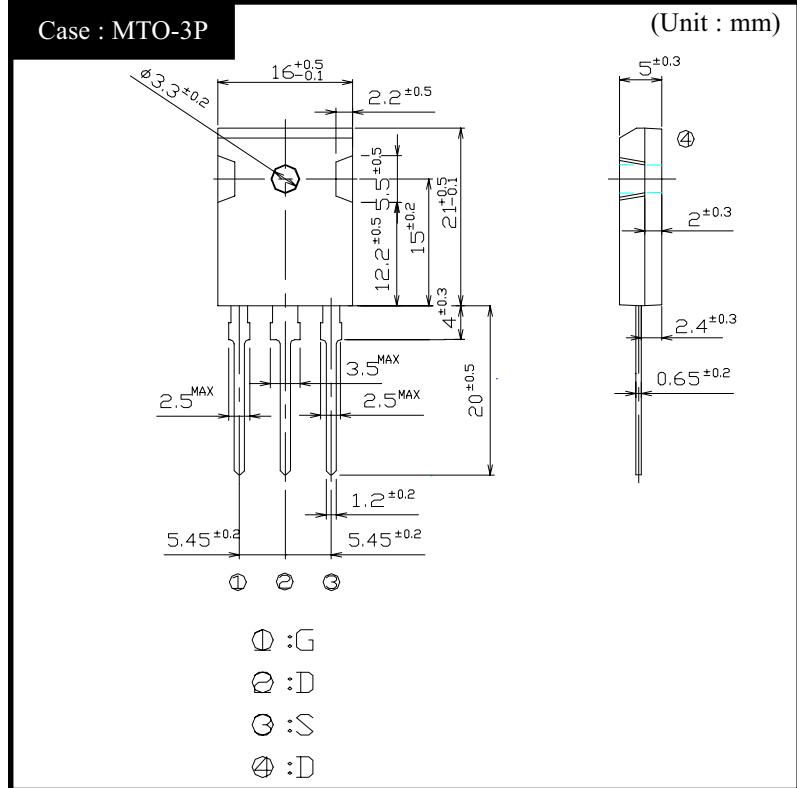
FEATURES

- Input capacitance (C_{iss}) is small.
Especially, input capacitance at 0 bias is small.
- The static $R_{ds(on)}$ is small.
- The switching time is fast.
- Avalanche resistance guaranteed.

APPLICATION

- Switching power supply of AC 240V input
- High voltage power supply
- Inverter

OUTLINE DIMENSIONS



RATINGS

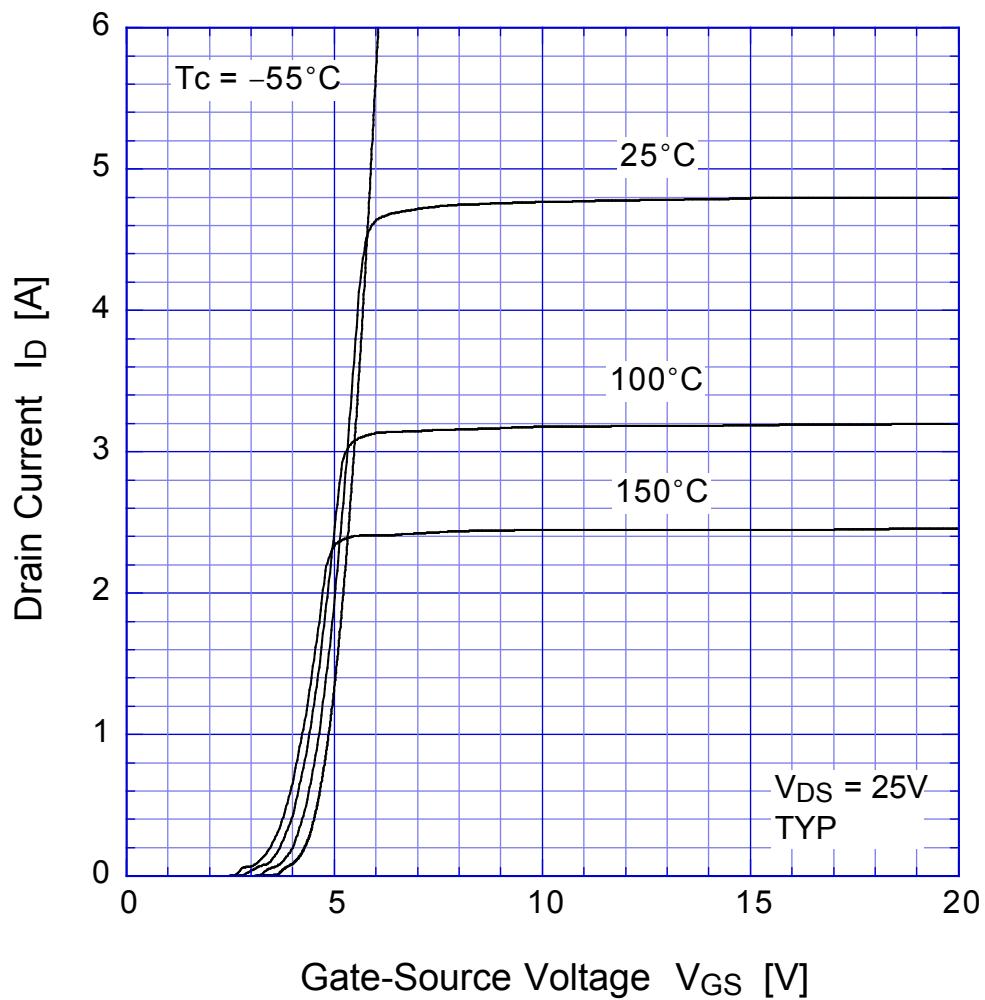
● Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T_{stg}		$-55 \sim 150$	$^\circ\text{C}$
Channel Temperature	T_{ch}		150	
Drain-Source Voltage	V_{DSS}		900	V
Gate-Source Voltage	V_{GSS}		± 30	
Continuous Drain Current(DC)	I_D		3	A
Continuous Drain Current(Peak)	I_{DP}	Pulse width $\leq 10 \mu\text{ s}$, Duty cycle $\leq 1/100$	6	
Continuous Source Current(DC)	I_S		3	
Total Power Dissipation	P_T		65	W
Repetitive Avalanche Current	I_{AR}	$T_{ch} = 150^\circ\text{C}$	3	A
Single Avalanche Energy	E_{AS}	$T_{ch} = 25^\circ\text{C}$	48	mJ
Repetitive Avalanche Energy	E_{AR}	$T_{ch} = 25^\circ\text{C}$	4.8	
Mounting Torque	T_{OR}	(Recommended torque : 0.5 N·m)	0.8	N·m

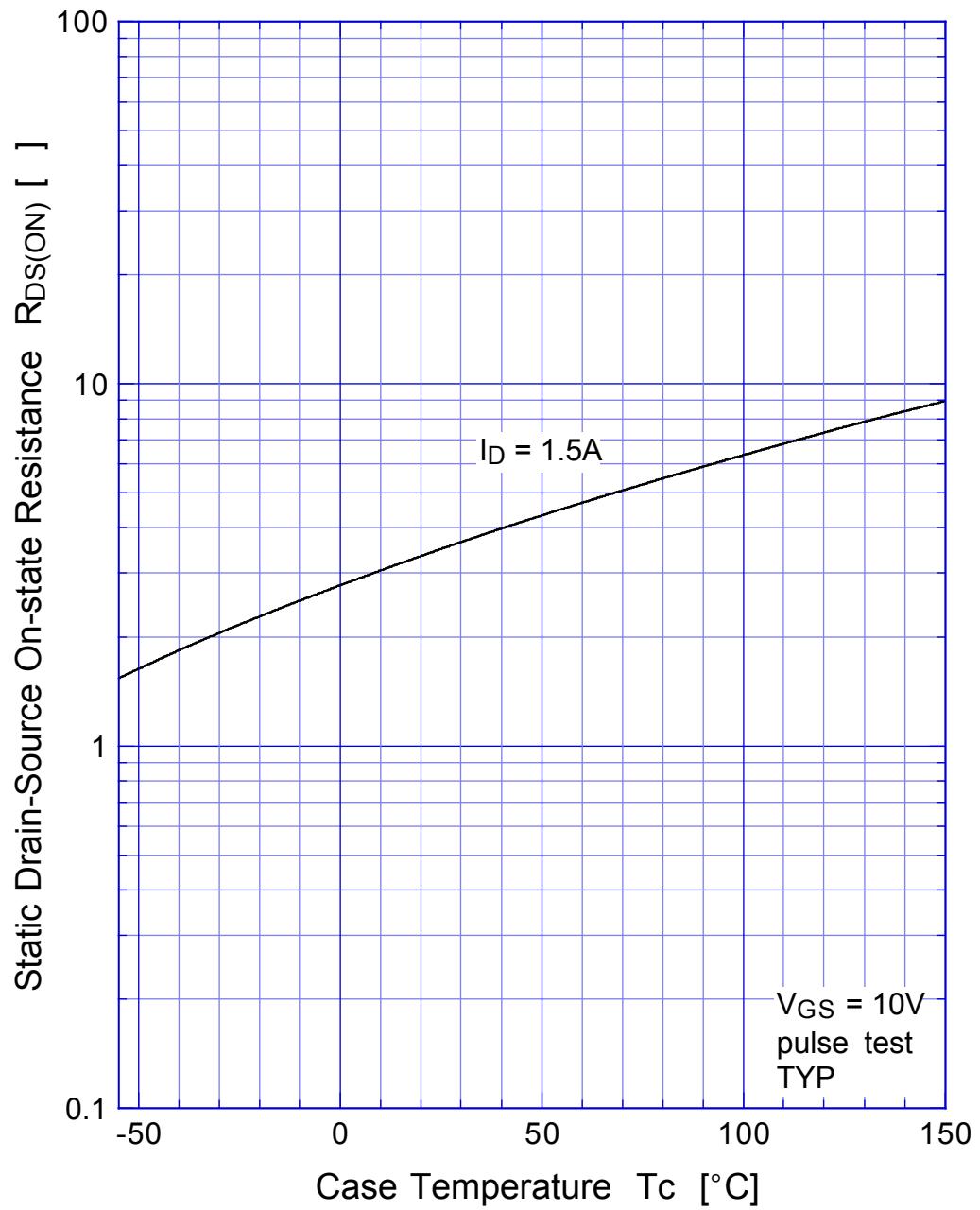
●Electrical Characteristics T_c = 25°C

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	ID = 1mA, V _{GS} = 0V	900			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 900V, V _{GS} = 0V			250	μ A
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V			±0.1	
Forward Transconductance	g _{fs}	ID = 1.5A, V _{DS} = 10V	1.5	2.5		S
Static Drain-Source On-state Resistance	R _{DSON}	ID = 1.5A, V _{GS} = 10V		3.5	4.7	Ω
Gate Threshold Voltage	V _{TH}	ID = 1mA, V _{DS} = 10V	2.5	3.0	3.5	V
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1.5A, V _{GS} = 0V			1.5	
Thermal Resistance	θ_{JC}	junction to case			1.92	°C/W
Total Gate Charge	Q _g	V _{DD} = 400V, V _{GS} = 10V, I _D = 3A		30		nC
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		630		pF
Reverse Transfer Capacitance	C _{rss}			16		
Output Capacitance	C _{oss}			67		
Turn-On Time	t _{on}	I _D = 1.5A, R _L = 100Ω, V _{GS} = 10V		40	70	ns
Turn-Off Time	t _{off}			140	230	

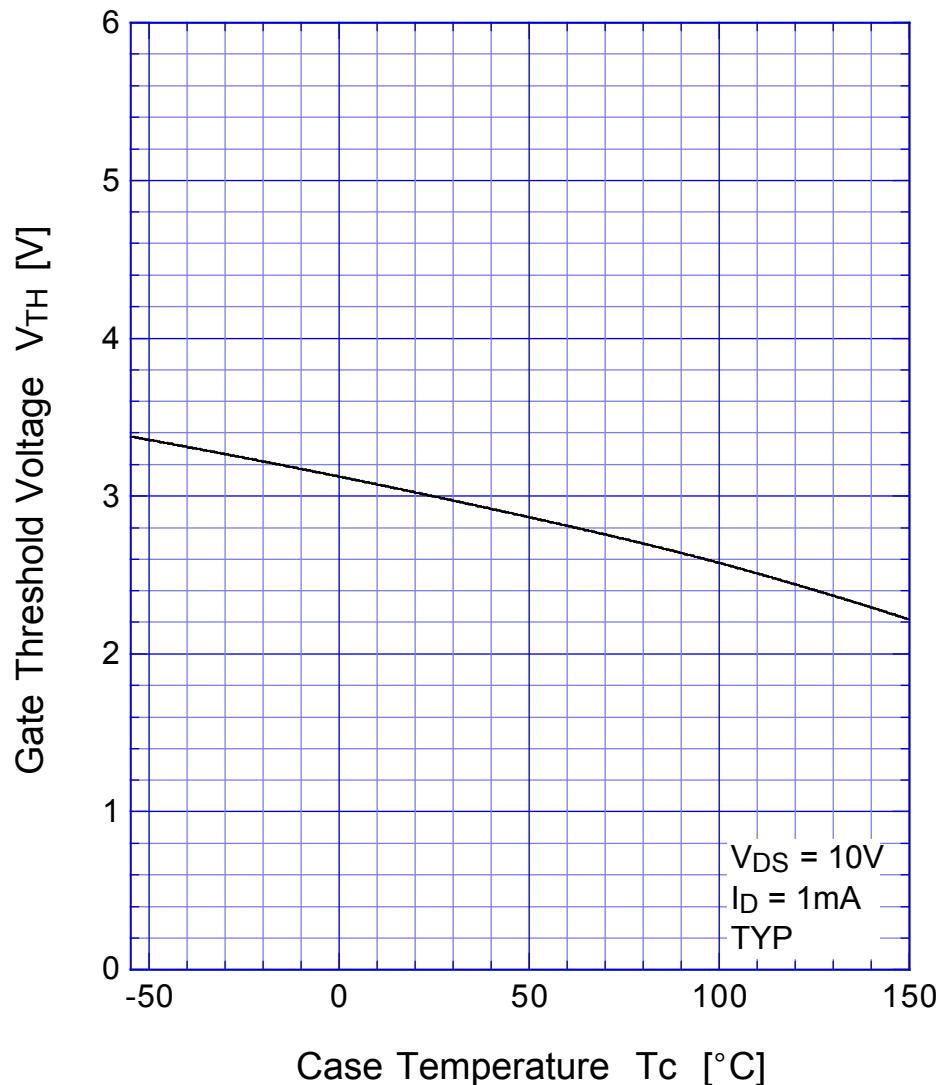
2SK2667 Transfer Characteristics



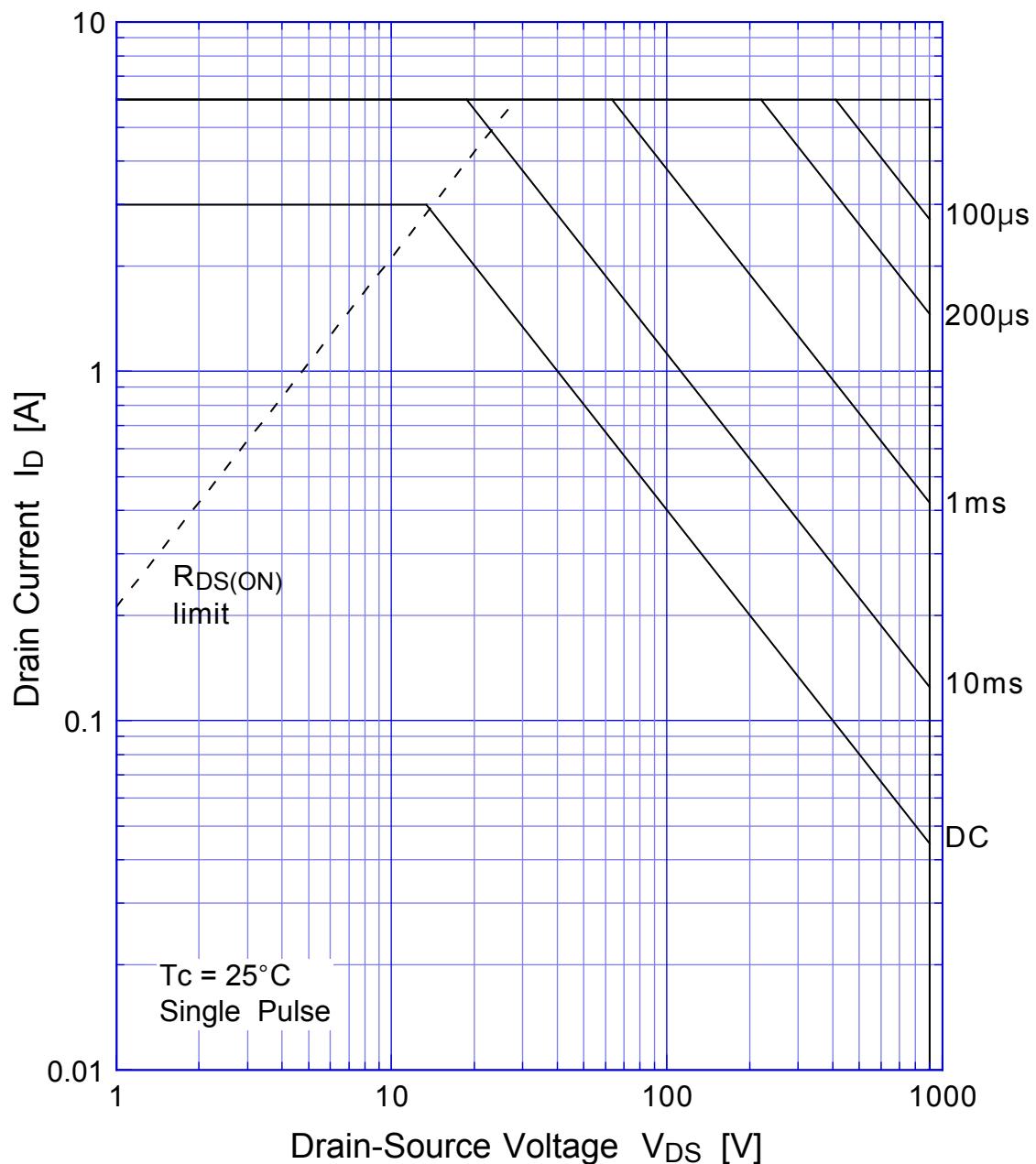
2SK2667 Static Drain-Source On-state Resistance



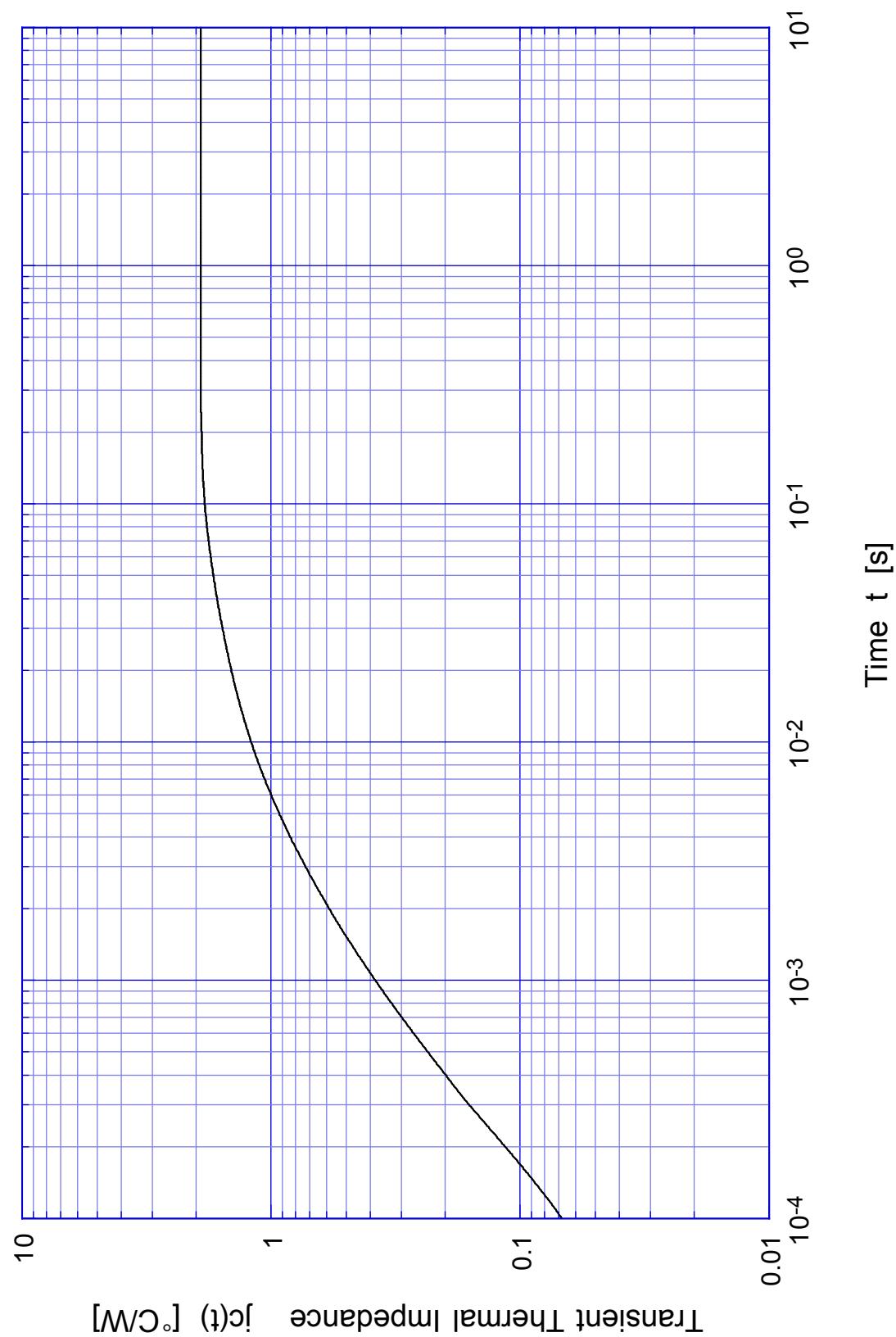
2SK2667 Gate Threshold Voltage



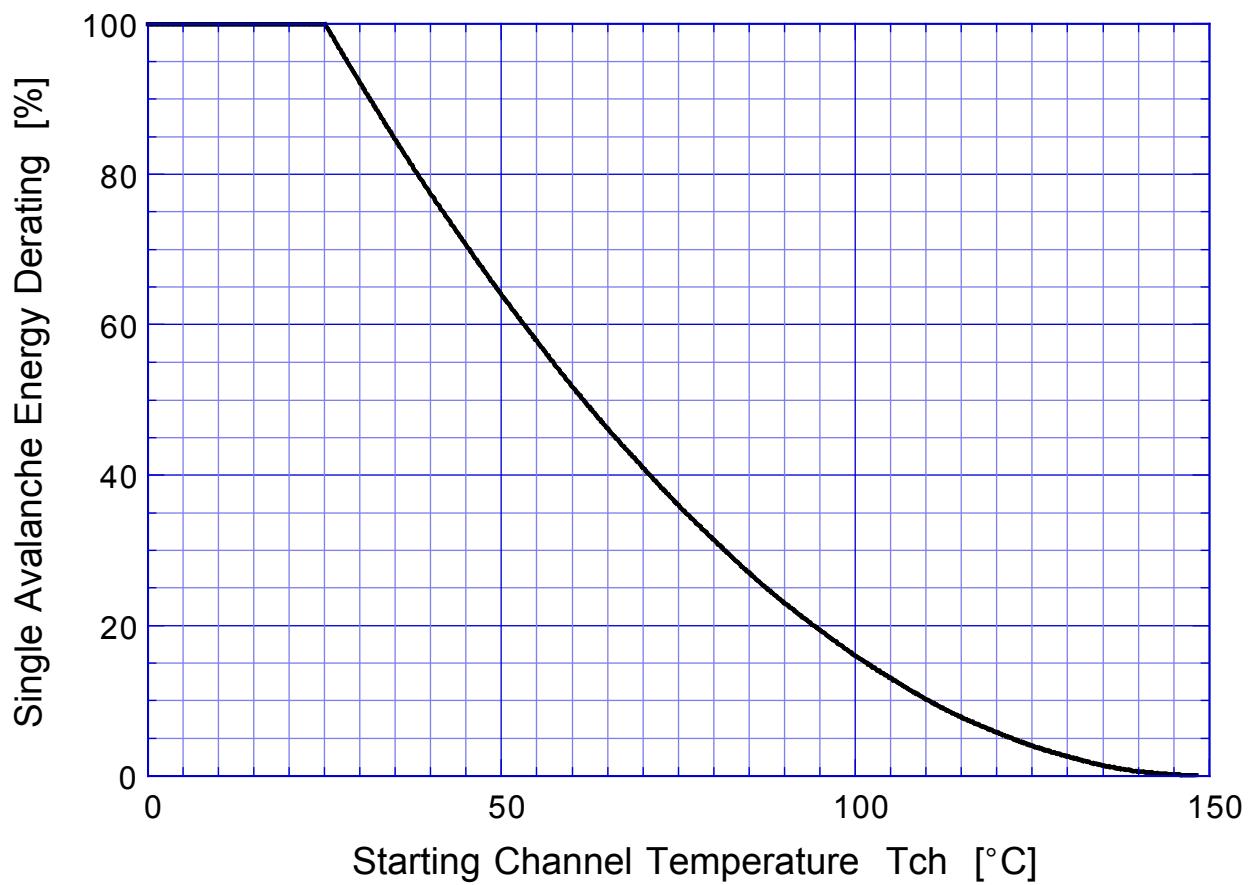
2SK2667 Safe Operating Area



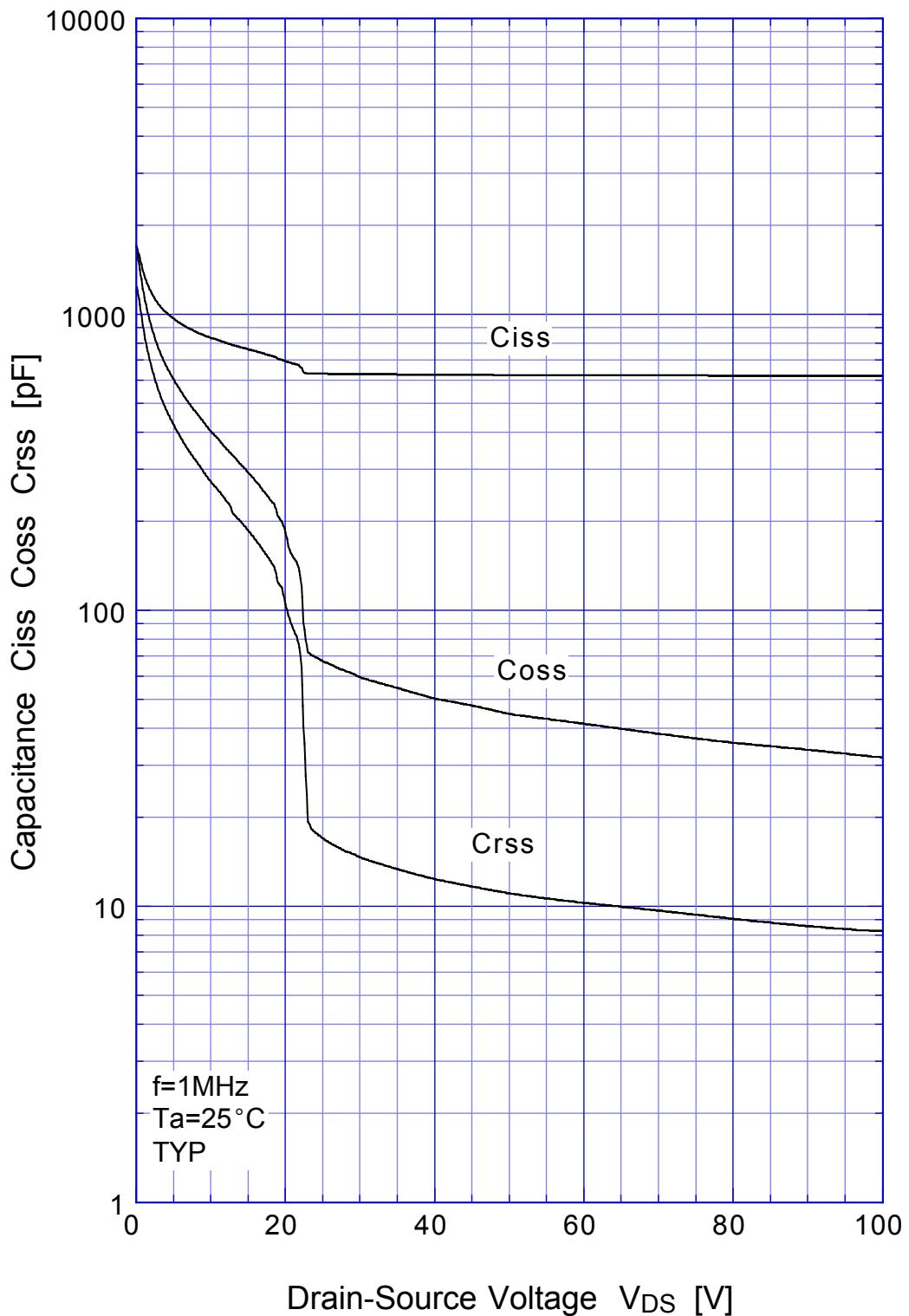
2SK2667 Transient Thermal Impedance



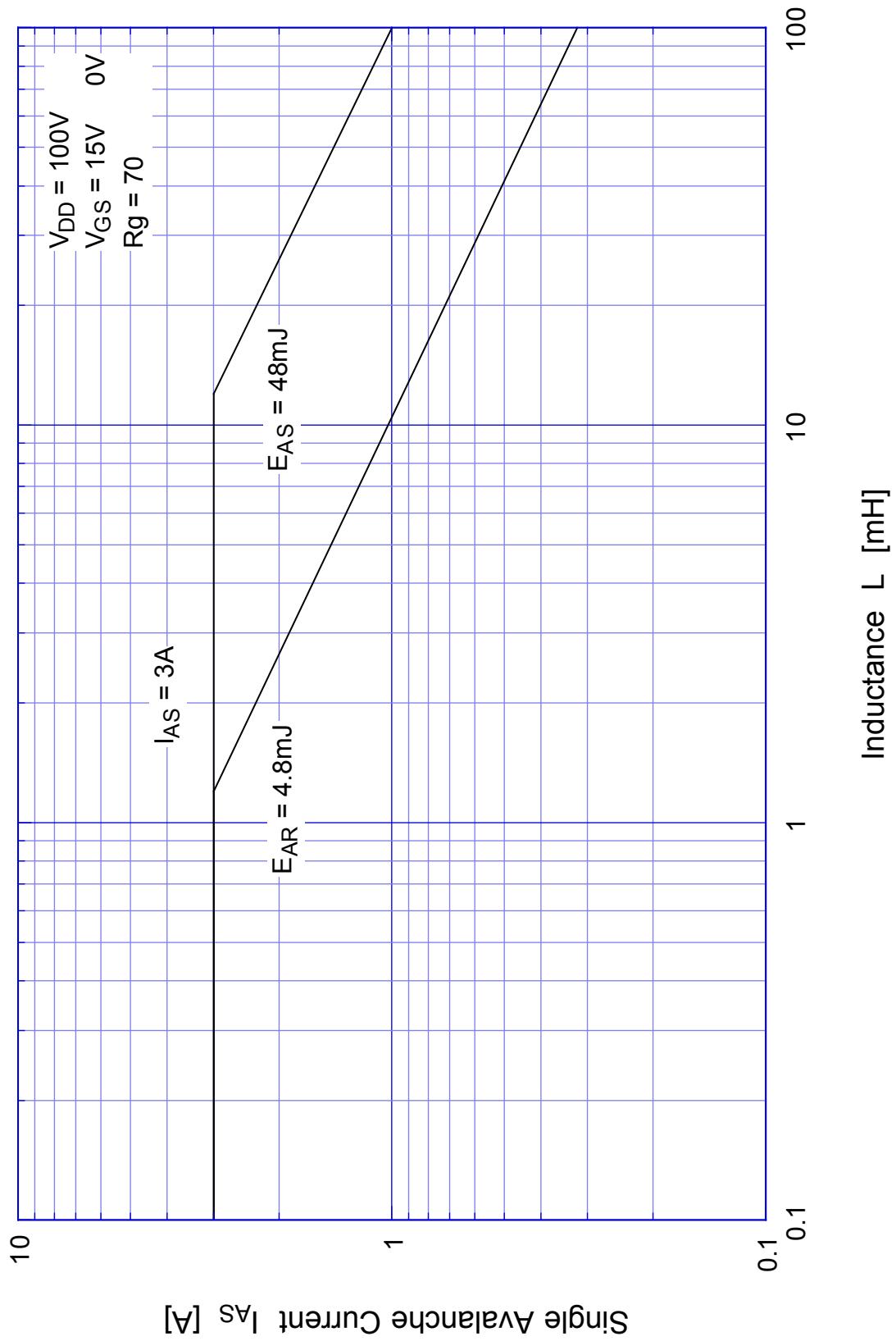
2SK2667 Single Avalanche Energy Derating



2SK2667 Capacitance

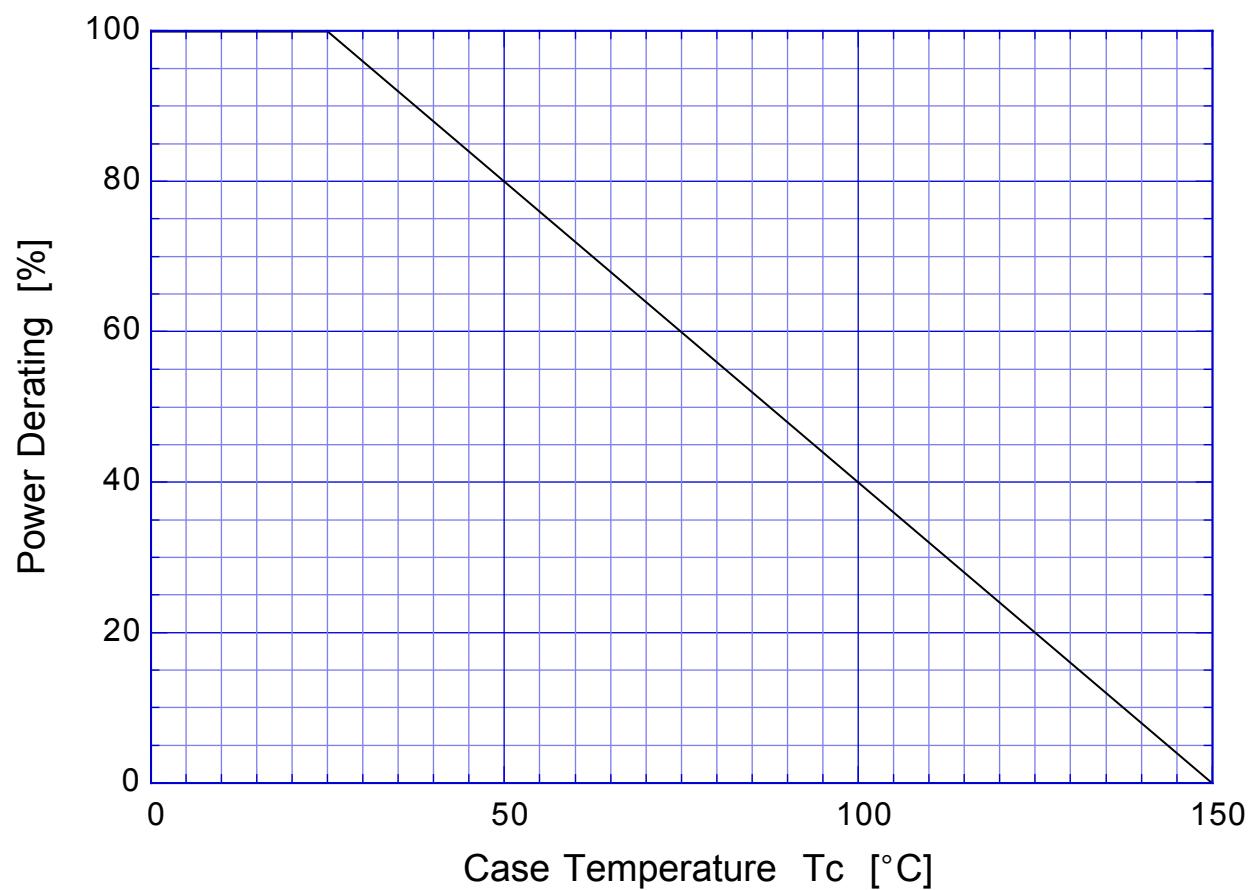


2SK2667 Single Avalanche Current - Inductive Load



2SK2667

Power Derating



2SK2667

Gate Charge Characteristics

